

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ASMMC.038AUSAPPLICATION NO.  
09/975,468INFORMATION DISCLOSURE STATEMENT  
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APPLICANT  
SOPHIE et al.FILING DATE  
October 9, 2001GROUP  
2812RECEIVED  
JAN 15 2003

TECHNOLOGY CENTER-2800

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
Ek ✓	1. SOI Technology: IBM's Next Advance In Chip Design. Date unknown.
✓	2. Fukuzumi, Y. et al., "Liner-Supported Cylinder (LSC) Technology to realize Ru/Ta <sub>2</sub> O <sub>5</sub> /Ru Capacitor for Future DRAMs," <u>IEEE, IED 2000, Session 34</u> (2000).
✓	3. Hones, P. et al., "MOCVD of Thin Ruthenium Oxide Films: Properties and Growth Kinetics," <u>Chem. Vap. Deposition</u> , Vol. 6, No. 4, pp. 193-198 (2000).
✓	4. Inoue, N. et al., "Low thermal-budget fabrication of sputtered-PZT capacitor on multilevel interconnects for embedded FeRAM," <u>IEEE, IED 2000, Session 34</u> (2000).
✓	5. Jung, D. et al., "A Novel Ir/IrO <sub>2</sub> /Pt-PZT-Pt/IrO <sub>2</sub> /Ir Capacitor for A Highly Reliable Mega-Scale FRAM," <u>IEEE, IED 2000, Session 34</u> , (2000).
✓	6. Solanki R. et al., "Atomic Layer Deposition of Copper Seed Layers," <u>Electrochemical and Solid-State Letters</u> , Vol. 3, No. 10, pp. 479-480 (2000).
✓	7. Sundani et al., "Oral presentation of dual damascene process, slides.
✓	8. Utriainen, M. et al., "Studies of metallic thin film growth in an atomic layer epitaxy reactor using M(acac) <sub>2</sub> (M = Ni, Cu, Pt) precursors," <u>Applied Surface Science</u> , Vol. 157, pp. 151-158 (2000).
✓	9. Won, Seok-Jun et al., "Conformal CVD-Ruthenium Process for MIM Capacitor in Giga-bit DRAMs," <u>IEEE, IED 2000, Session 34</u> (2000).
✓	10. Xu, P. et al., "A Breakthrough in Low-k Barrier/Etch Stop Films for Copper Damascene Applications," <u>Semiconductor Fabtech</u> , 11th Edition, p. 239 (2000).
✓	11. Yoon, Dong-Soo et al., "Investigation of RuO <sub>2</sub> -Incorporated Pt Layer as a Bottom Electrode and Diffusion Barrier for High Epsilon Capacitor Applications," <u>Electrochemical and Solid-State Letters</u> , Vol. 3, No. 8, pp. 373-376 (2000).

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EXAMINER <i>Em Han</i>	DATE CONSIDERED <i>3/30/04</i>
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APPLICANT  
Sophia et al.FILING DATE  
October 9, 2001GROUP  
2813

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
EK	1	5,939,334	08/17/99	Nguyen et al.	438	689	

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
EK	2	Poster presentation. Soininen. P. and Elers. K.E.. Advanced Metallization Conference, October 8-11, 2001, Montreal, Canada
EK	3	Satta et al., "The Removal of Copper Oxides by Ethyl Alcohol Monitored in Situ by Spectroscopic Ellipsometry," Journal of The Electromechanical Society, 150 (5), pp. 300-306 (2003)

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031104

EXAMINER <i>Erik K...</i>	DATE CONSIDERED <i>3/30/04</i>
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